

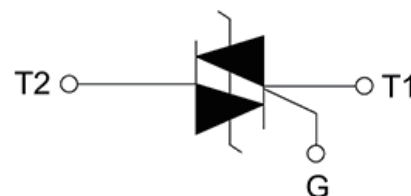
## DESCRIPTION:

The chip triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. The chip embeds a TVS structure to absorb the inductive turn-off energy such as those described in the IEC 61000-4-5 standards. At the same time, the triac shields the positive signal trigger to reduce the probability of product misoperation. It is triggered with a negative gate current flowing out of the gate pin.



## MAIN FEATURES

| Symbol             | Value    | Unit |
|--------------------|----------|------|
| $I_{T(RMS)}$       | 6        | A    |
| $V_{DRM}/V_{RRM}$  | 1000     | V    |
| $I_{GT\ I/II/III}$ | 10/10/10 | mA   |



## ABSOLUTE MAXIMUM RATINGS

| Parameter                                                                                                        | Symbol       | Value   | Unit                   |
|------------------------------------------------------------------------------------------------------------------|--------------|---------|------------------------|
| Storage junction temperature range                                                                               | $T_{stg}$    | -40-150 | °C                     |
| Operating junction temperature range                                                                             | $T_j$        | -40-125 | °C                     |
| Repetitive peak off-state voltage ( $T_j=25^\circ\text{C}$ )                                                     | $V_{DRM}$    | 1000    | V                      |
| Repetitive peak reverse voltage ( $T_j=25^\circ\text{C}$ )                                                       | $V_{RRM}$    | 1000    | V                      |
| RMS on-state current ( $T_c \leq 98^\circ\text{C}$ )                                                             | $I_{T(RMS)}$ | 6       | A                      |
| Non repetitive surge peak on-state current (full cycle , $t_p=20\text{ms}$ , $T_j=25^\circ\text{C}$ )            | $I_{TSM}$    | 60      | A                      |
| Non repetitive surge peak on-state current (full cycle , $t_p=16.6\text{ms}$ , $T_j=25^\circ\text{C}$ )          |              | 66      |                        |
| $I^2t$ value for fusing ( $t_p=10\text{ms}$ , $T_j=25^\circ\text{C}$ )                                           | $I^2t$       | 18      | $\text{A}^2\text{s}$   |
| Critical rate of rise of on-state current ( $I_G=2 \times I_{GT}$ , $f=100\text{Hz}$ , $T_j=125^\circ\text{C}$ ) | $di/dt$      | 100     | $\text{A}/\mu\text{s}$ |
| Peak gate current ( $t_p=20\mu\text{s}$ , $T_j=125^\circ\text{C}$ )                                              | $I_{GM}$     | 4       | A                      |

|                                                                                      |             |     |    |
|--------------------------------------------------------------------------------------|-------------|-----|----|
| Average gate power dissipation ( $T_j=125^{\circ}\text{C}$ )                         | $P_{G(AV)}$ | 0.5 | W  |
| Peak gate power                                                                      | $P_{GM}$    | 10  | W  |
| Peak pulse voltage<br>( $T_j=25^{\circ}\text{C}$ ; non-repetitive, off-state; FIG.7) | $V_{pp}$    | 3.5 | kV |

**ELECTRICAL CHARACTERISTICS** ( $T_j=25^{\circ}\text{C}$  unless otherwise specified)

| Symbol      | Test Condition                                                                   | Quadrant    | Value |      | Unit             |
|-------------|----------------------------------------------------------------------------------|-------------|-------|------|------------------|
| $I_{GT}$    | $V_D=12\text{V } R_L=33\Omega$                                                   | I - II -III | MAX.  | 10   | mA               |
| $V_{GT}$    |                                                                                  | I - II -III | MAX.  | 1    | V                |
| $V_{GD}$    | $V_D=V_{DRM} T_j=125^{\circ}\text{C}$<br>$R_L=3.3\text{k}\Omega$                 | I - II -III | MIN.  | 0.2  | V                |
| $I_L$       | $I_G=1.2I_{GT}$                                                                  | I -III      | MAX.  | 20   | mA               |
|             |                                                                                  | II          |       | 35   |                  |
| $I_H$       | $I_T=100\text{mA}$                                                               |             | MAX.  | 20   | mA               |
| $dV/dt$     | $V_D=670\text{V}$ Gate Open $T_j=125^{\circ}\text{C}$                            |             | MIN.  | 300  | V/ $\mu\text{s}$ |
| $(dI/dt)_c$ | $(dV/dt)_c=10\text{V}/\mu\text{s}$ , $T_j=125^{\circ}\text{C}$                   |             | MIN.  | 3    | A/ms             |
| $t_{on}$    | $I_G=20\text{mA } I_A=200\text{mA } I_R=20\text{mA}$<br>$T_j=25^{\circ}\text{C}$ |             | TYP.  | 4    | $\mu\text{s}$    |
| $t_{off}$   |                                                                                  |             |       | 50   |                  |
| $V_{CL}$    | $I_{CL}=0.1\text{mA } t_p=1\text{ms}$                                            |             | MIN.  | 1050 | V                |

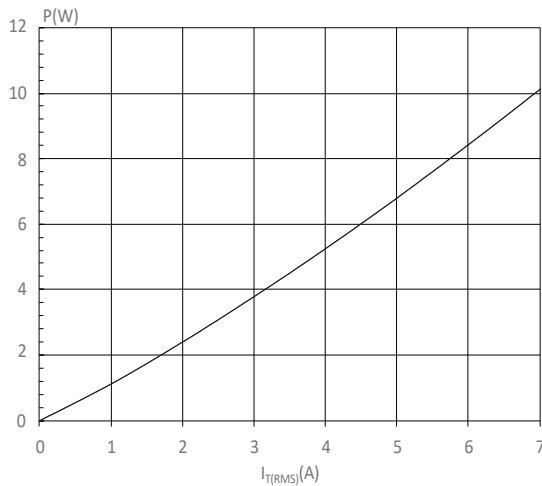
**STATIC CHARACTERISTICS**

| Symbol    | Parameter                                |                           | Value(MAX.) | Unit          |
|-----------|------------------------------------------|---------------------------|-------------|---------------|
| $V_{TM}$  | $I_{TM}=8.5\text{A } t_p=380\mu\text{s}$ | $T_j=25^{\circ}\text{C}$  | 1.5         | V             |
| $V_{TO}$  | Threshold voltage                        | $T_j=125^{\circ}\text{C}$ | 0.82        | V             |
| $R_D$     | Dynamic resistance                       | $T_j=125^{\circ}\text{C}$ | 64          | m $\Omega$    |
| $I_{DRM}$ | $V_D=V_{DRM} V_R=V_{RRM}$                | $T_j=25^{\circ}\text{C}$  | 8           | $\mu\text{A}$ |
| $I_{RRM}$ |                                          | $T_j=125^{\circ}\text{C}$ | 0.5         | mA            |

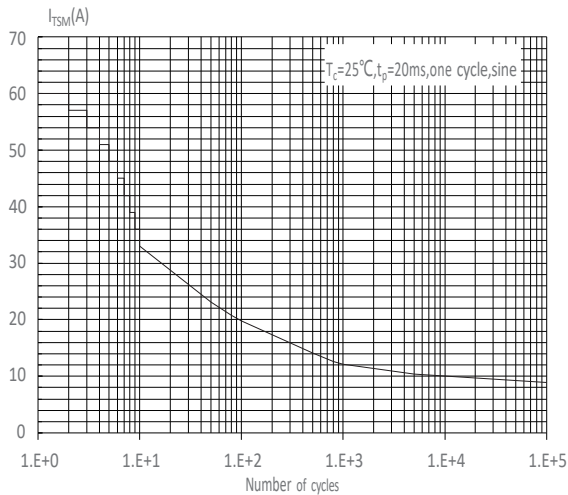
**THERMAL RESISTANCES**

| Symbol        | Parameter                | Value | Unit                        |
|---------------|--------------------------|-------|-----------------------------|
| $R_{th(j-c)}$ | junction to case (AC)    | 3.2   | $^{\circ}\text{C}/\text{W}$ |
| $R_{th(j-a)}$ | junction to ambient (AC) | 60    | $^{\circ}\text{C}/\text{W}$ |

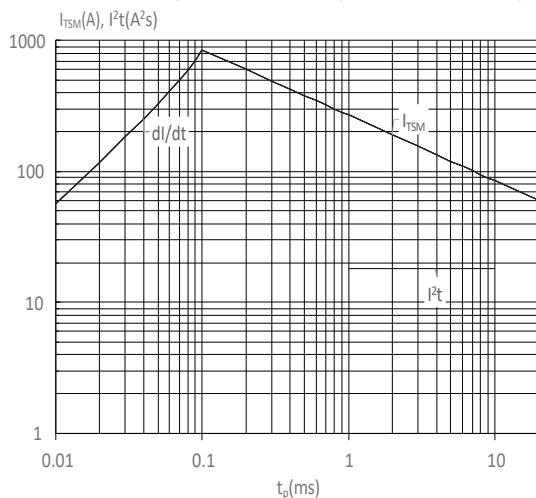
**FIG :** Maximum power dissipation versus RMS on-state current



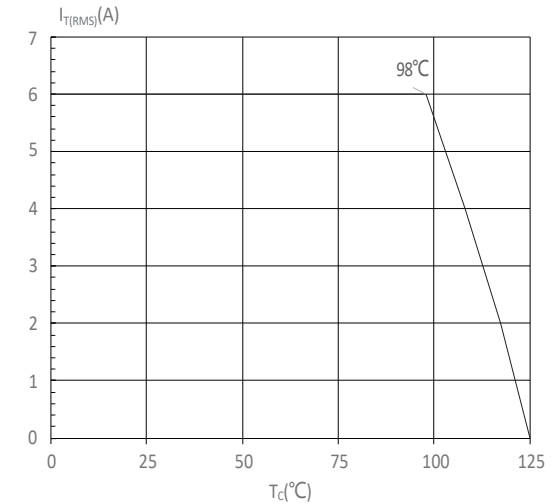
**FIG :** Surge peak on-state current versus number of cycles



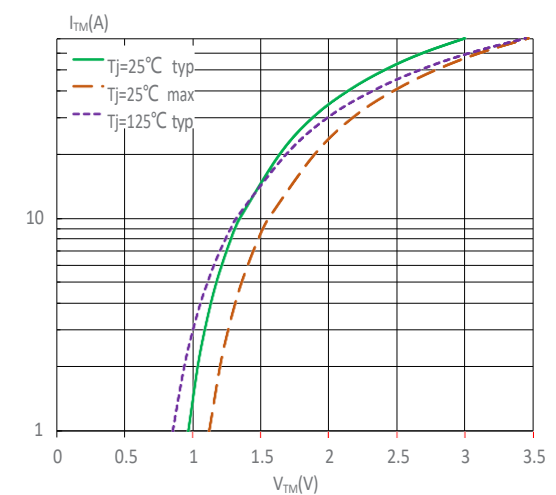
**FIG :** Non-repetitive surge peak on-state current for a sinusoidal pulse with width  $t_p < 20ms$ , and corresponding value of  $I^2t$  ( $di/dt < 100A/\mu s$ )



**FIG :** RMS on-state current versus case temperature



**FIG :** On-state characteristics



**FIG :** Relative variations of gate trigger current, holding current and latching current versus junction temperature

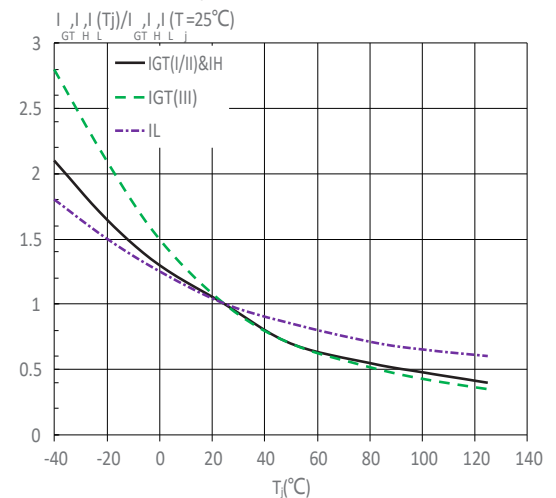
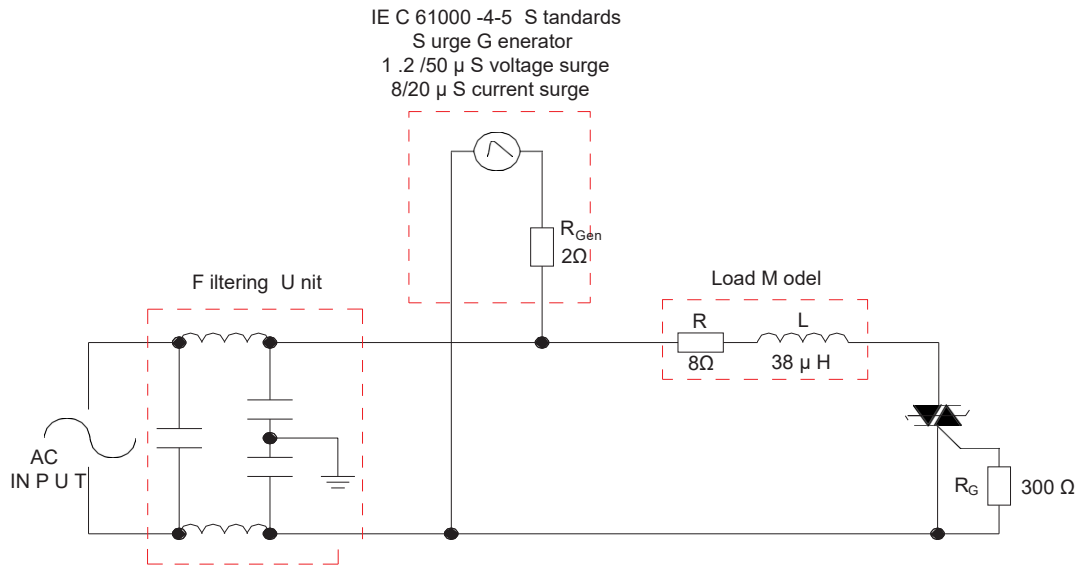


FIG : Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



## LEAD FORMING AND SOLDERING

Refer to the application note “Assembly Instructions for Thyristors in Through-hole Package” released by JieJie Microelectronics.